material (e.g., solid polycrystalline silicon) that exits the dumper 202 when opened and flows through the growth chamber outlet 110 and into the crucible 104. The polycrystalline semiconductor material exiting the dumper 202 is indicated by the arrows 208 in FIG. 2.

[0038] In the example ingot puller 100, the dumper 202 is connectable with the pull wire 124 (e.g., via the pulling assembly 126) and the winch 132 is operable to raise and lower the dumper 202 in the ingot receiving chamber 162. The ingot receiving vessel 160 includes an end cap 178 that is integral with or connected to the sidewall 172 at the second vessel end 168 (e.g., using fasteners). The winch 132 is seated on the end cap 178 and the pull wire 124 extends through the end cap 178. The winch 132 is used to lower and raise the dumper 202 during a charging operation and to lower the seed crystal 130 and raise the seed crystal 130 and growing ingot during an ingot growth process. In other examples, a different pulling mechanism (e.g., a different pulling winch) may be used between the charging operation and the ingot growth process.

[0039] The dumper 202 includes a sidewall 210 (also referred to as a dumper sidewall 210) and a bottom 212 (also referred to as a dumper bottom 212). The sidewall 210 and the bottom 212 define an interior volume 230 of the dumper 202 that is sized to contain a suitable amount of polycrystalline semiconductor material for charging into the crucible 104 and subsequently forming the melt 102. The sidewall 210 defines a circumferential and longitudinal size and cross-sectional shape of the dumper 202. The sidewall 210 has any suitable cross-sectional shape, for example, the sidewall 210 may be cylindrical, prismatic, frusto-conical,